

# DEC

## SBP820 THRU SBP8100

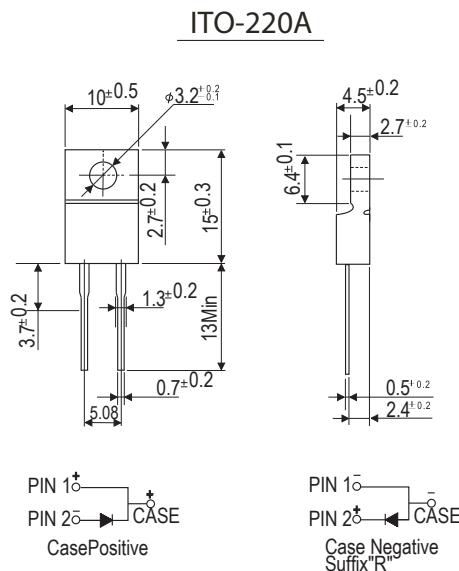
CURRENT 8.0Amperes  
VOLTAGE 20 to 100 Volts

### Features

- Plastic Package has Underwriters Laboratory Flammability Classification 94V-0
- Metal silicon junction, majority carrier conduction
- Guard ring for overvoltage protection
- Low power loss, high efficiency
- High current capability, Low forward voltage drop
- Single rectifier construction
- High surge capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications
- High temperature soldering guaranteed:  
250 °C/10 seconds, 0.25" (6.35mm) from case

### Mechanical Data

- Case : JEDEC ITO-220A molded plastic body
- Terminals : Lead solderable per MIL-STD-750, Method 2026
- Polarity : As marked
- Mounting Position : Any
- Weight : 0.08 ounce, 2.24 grams



Dimensions in inches and (millimeters)

### Maximum Ratings and Electrical Characteristics

(Ratings at 25 °C ambient temperature unless otherwise specified, single phase, half wave, resistive or inductive load. For capacitive load, derate by 20%)

	Symbols	SBP 820	SBP 830	SBP 840	SBP 850	SBP 860	SBP 880	SBP 8100	Units
Maximum repetitive peak reverse voltage	V <sub>RRM</sub>	20	30	40	50	60	80	100	Volts
Maximum RMS voltage	V <sub>RMS</sub>	14	21	28	35	42	56	70	Volts
Maximum DC blocking voltage	V <sub>DC</sub>	20	30	40	50	60	80	100	Volts
Maximum average forward rectified current (see Fig. 1)	I <sub>(AV)</sub>								Amps
Repetitive peak forward current(square wavr, 20KHZ) at T <sub>c</sub> =105 °C	I <sub>FRM</sub>								Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	I <sub>FSM</sub>								Amps
Maximum instantaneous forward voltage at 8.0A (Note 1)	V <sub>F</sub>		0.65		0.75		0.80	0.85	Volts
Maximum instantaneous reverse current at rated DC blocking voltage (Note1)	T <sub>A</sub> =25 °C	I <sub>R</sub>			1.0				mA
	T <sub>A</sub> =125 °C			15		50			
Typical thermal resistance (Note 2)	R <sub>θJC</sub>			5.0					°C/W
Operating junction temperature range	T <sub>J</sub>		-65 to +125		-65 to +150				°C
Storage temperature range	T <sub>STG</sub>			-65 to +150					°C

#### Notes:

- Pulse test: 300μS pulse width, 1% duty cycle
- Thermal resistance from junction to case

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## RATINGS AND CHARACTERISTIC CURVES SBP820 THRU SBP8100

FIG.1-FORWARD CURRENT DERATING CURVE

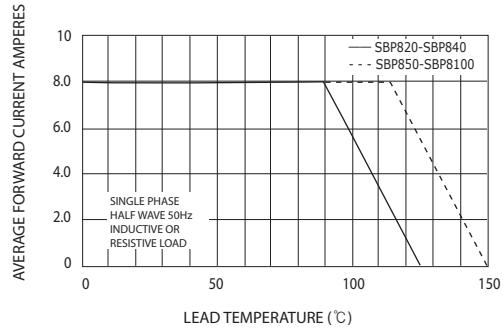


FIG.4-TYPICAL JUNCTION CAPACITANCE

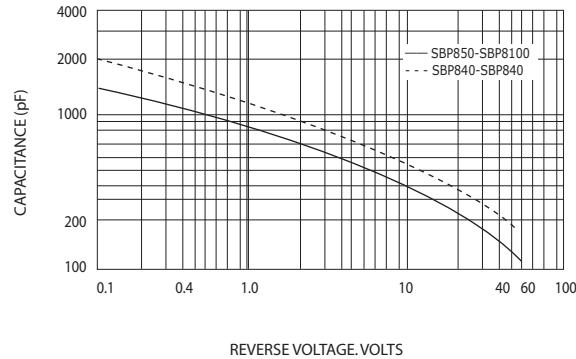


FIG.5-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

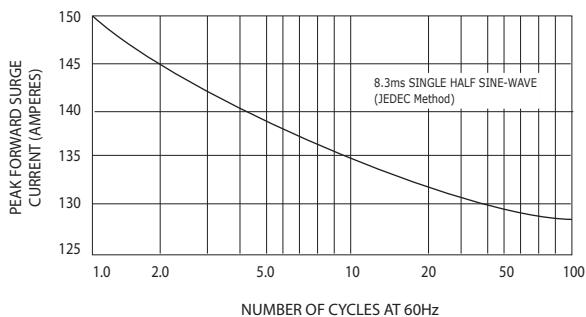


FIG.2-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

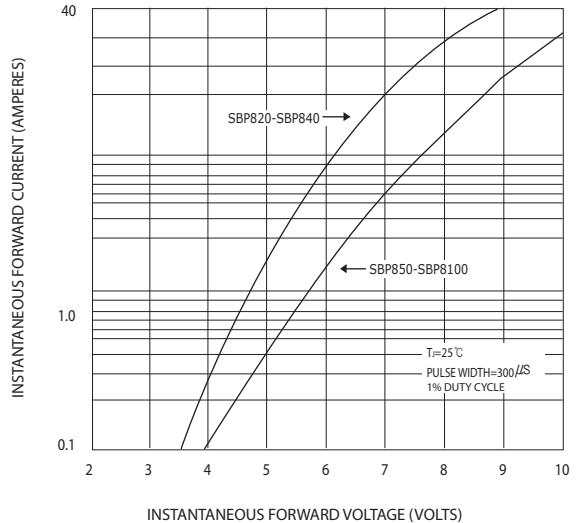


FIG.3-TYPICAL REVERSE CHARACTERISTICS

